

ABSTRACT

A field effect transistor includes a semiconductor layer structure including GaN channel layer 12 and AlGa electron supply layer 13, source electrode 1 and drain electrode 3 which are formed on electron supply layer 13 so as to be separated from each other, gate electrode 2 formed between source electrode 1 and drain electrode 3, and SiON film 23 formed on electron supply layer 13. Gate electrode 2 has a field plate portion 5 that projects toward drain electrode 3 in the form of an eave on SiON film 23. The thickness of a portion (field plate layer 23a) of SiON film 23 lying between field plate portion 5 and electron supply layer 13 gradually increases from gate electrode 2 to drain electrode 3.